



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

RB521S-30

SOD-523 Schottky Barrier Diode 肖特基势垒二极管

Internal Configuration & Device Marking 内部结构与产品打标

Type 型号	RB521S-30
Pin 管脚	
Mark 打标	

Absolute Maximum Ratings 最大额定值

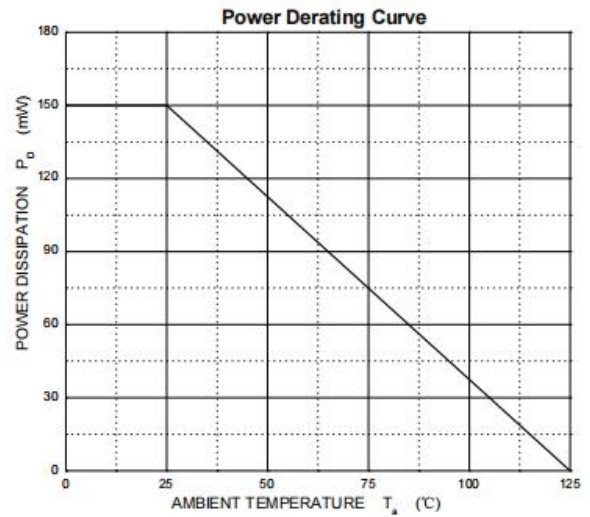
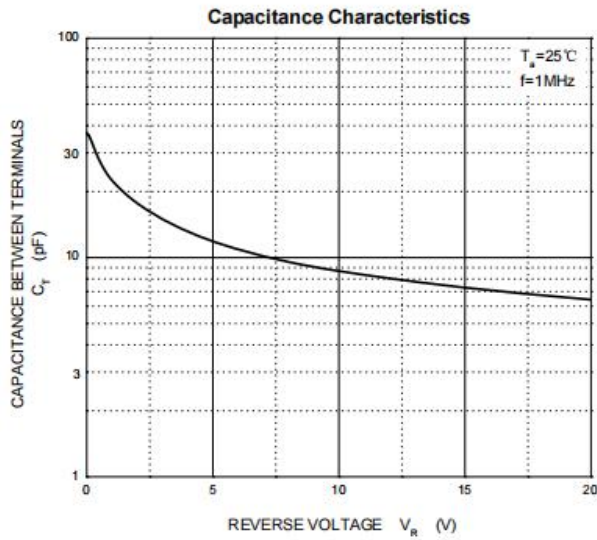
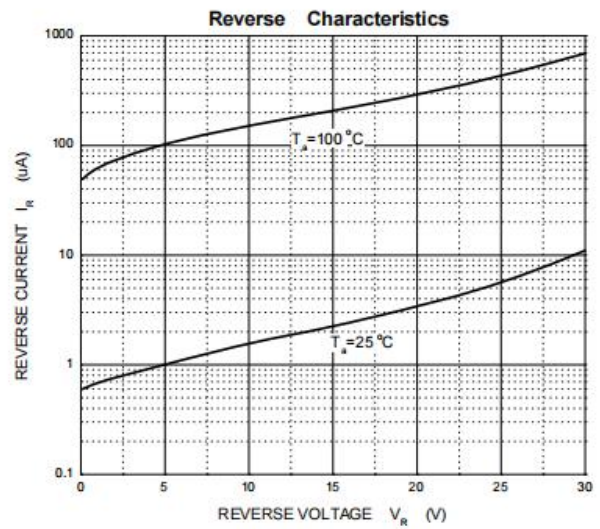
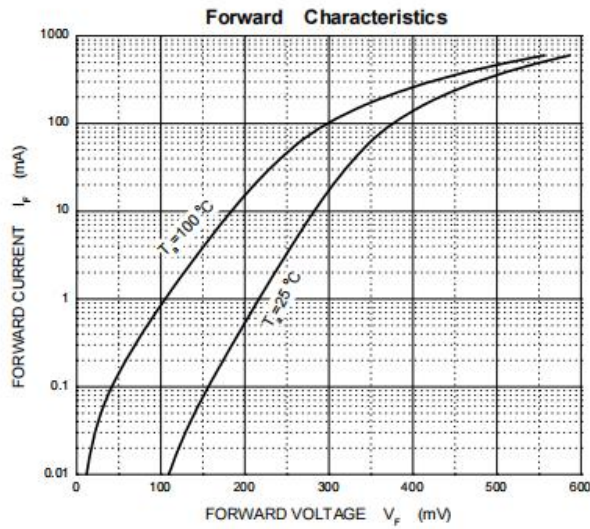
Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
DC Reverse Voltage 直流反向电压	V_R	30	
Forward Work Current 正向工作电流	I_o	200	mA
Peak Forward Surge Current 正向峰值浪涌电流	I_{FSM}	1000	mA
Power dissipation 耗散功率	$P_D(T_a=25^\circ C)$	150	mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	668	$^\circ C/W$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+125 $^\circ C$	

Electrical Characteristics 电特性

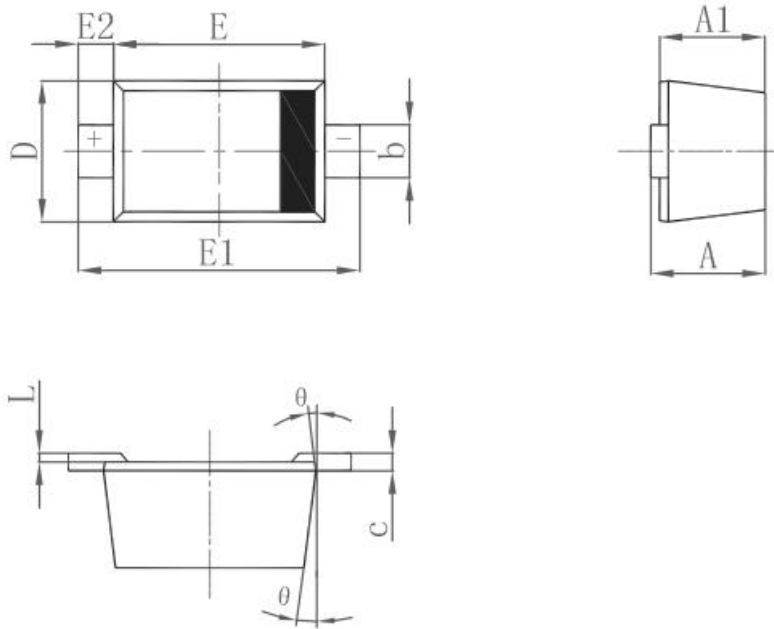
($T_A=25^\circ C$ unless otherwise noted 如无特殊说明, 温度为 $25^\circ C$)

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压($I_R=100\mu A$)	$V_{(BR)}$	30	—	V
Reverse Leakage Current 反向漏电流($V_R=10V$)	I_R	—	30	μA
Forward Voltage($I_F=10mA$) 正向电压($I_F=200mA$)	V_F	—	0.35 0.5	V

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.510	0.770	0.020	0.031
A1	0.500	0.700	0.020	0.028
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	0.750	0.850	0.030	0.033
E	1.100	1.300	0.043	0.051
E1	1.500	1.700	0.059	0.067
E2	0.200 REF		0.008 REF	
L	0.010	0.070	0.001	0.003
θ	7° REF		7° REF	